

SANYO SEMICONDUCTOR

2SC2271

2SC2271 — NPN Triple Diffused Planar Type Silicon Transistor
For Picture Output or Driver of H-Deflection

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	VCBO	300	V
Collector to Emitter Voltage	VCEO	300	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	100	mA
	icp	300	mA
Power Dissipation	PC	750	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

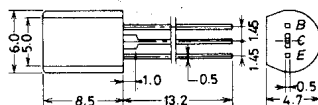
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cut Off Current	ICBO	V _{CB} =200V, I _E =0			1.0	uA
Emitter Cut Off Current	IEBO	VEB=6V, I _C =0			1.0	uA
DC Current Gain	h _{FE} *	V _{CE} =10V, I _C =10mA	40*		200*	
Gain Band Width Product	f _T	V _{CE} =30V, I _C =10mA	50			MHz
Output Capacitance	cob	V _{CB} =10V, f=1MHz			7.5	pF
C-E Saturation Voltage	V _{CE} (sat)	I _C =20mA, I _B =2mA			0.6	V
B-E Saturation Voltage	V _{BE} (sat)				1.0	V

h_{FE}* is classified as follows:

2SC2271 C:	40	80
2SC2271 D:	60	120
2SC2271 E:	100	200

Case Outline(unit:mm)



EIAJ: SC-51
SANYO: MP

B: Base
C: Collector
E: Emitter